

## **Prof. MEHMET KASAP**

### **Personal Information**

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### **Education Information**

Doctorate, University of Surrey, England 1990 - 1994

Post Graduate, Gazi University, Fen Bilimleri Enstitüsü, Fizik (YI) (Tezli), Turkey 1985 - 1989

Under Graduate, Firat University, Fen-Edebiyat Fakültesi, Fizik Mühendisliği Pr., Turkey 1981 - 1985

### **Dissertations**

Doctorate, Temperature and Pressure Dependent of Electron Transport in Plasticly Relaxed  $In_xGa_{1-x}As$ , University of Surrey, 1994

Post Graduate, Enerji band hesaplamalarında APW metodu ve bazı geçiş elementlerine uygulanması, Gazi University, Fen Bilimleri Enstitüsü, Fizik (YI) (Tezli), 1988

### **Research Areas**

Surfaces, Interfaces, Thin Films and Nanosystems, Electronic structure of bulk material, Electrical properties of electronic structures, interfaces, thin films and low-dimensional structures, Magnetic Properties and Materials, Optical Properties, Spectroscopy of Matter, Electronic transport in condensed matter

### **Academic Titles / Tasks**

Professor, Gazi University, Fen Fakültesi, Fizik Bölümü, 2006 - Continues

Associate Professor, Gazi University, Fen Fakültesi, Fizik Bölümü, 2000 - 2006

Assistant Professor, Gazi University, Fen Fakültesi, Fizik Bölümü, 1996 - 2000

Research Assistant, Gazi University, Fen Fakültesi, Fizik Bölümü, 1985 - 1996

### **Courses**

YARIİLETKEN FİZİĞİ, Under Graduate, 2016 - 2017, 2017 - 2018

TEMEL FİZİK II (ELEKTRİK), Under Graduate, 2017 - 2018

Maddenin Özellikleri, Under Graduate, 2017 - 2018

YARIİLETKEN FİZİĞİ, Post Graduate, 2016 - 2017, 2017 - 2018

TEMEL FİZİK I (MEKANİK), Under Graduate, 2016 - 2017, 2017 - 2018

### **Advising Theses**

KASAP M., Forensic Sciences In Terms Of Shot Residue Analysis Techniques And Forensic Applications, Doctorate,

İ.KARA(Student), 2014

KASAP M., Electron Transport Properties Of InGaN And GaN Quantum Well InAlN/GaN High Electron Mobility Transistor, Post Graduate, P.NARİN(Student), 2014

KASAP M., The investigation of temperature dependent electrical transport properties of In<sub>x</sub>Ga<sub>1-x</sub>P/GaAs, Post Graduate, E.BOYALI(Student), 2013

KASAP M., Temperature dependent electrical properties of high doped In<sub>x</sub>Ga<sub>1-x</sub>As alloy semiconductor, Post Graduate, E.YAZBAHAR(Student), 2012

KASAP M., Electron and magnetotransport properties of InAlN/GaN based high electron mobility transistors (HEMT), Doctorate, P.TUNAY(Student), 2010

KASAP M., AlGaIn/GaN TEMELLİ YÜKSEK ELEKTRON HAREKETLİLİKLİ TRANSİSTÖRLERİN (HEMT) ELEKTRON VE MANYETO İLETİM ÖZELLİKLERİ, S.Bora(Student), 2008

KASAP M., AlGaIn/GaN temelli yüksek elektron hareketlilikli transistörlerin (HEMT) elektron ve manyeto iletim özellikleri, Doctorate, S.BORA(Student), 2008

KASAP M., ELECTRON TRANSPORT PROPERTIES OF In<sub>x</sub>Ga<sub>1-x</sub>N, Doctorate, A.YILDIZ(Student), 2008

KASAP M., LEC tekniği ile büyütülen Zn katkılı InAs yarıiletkeninde sıcaklık bağımlı manyetik ve elektron iletim özellikleri, Post Graduate, İ.KARA(Student), 2006

KASAP M., MBE tekniği ile büyütülen InGaAs/GaAs ve AlGaAs yarıiletkenlerinin iletim özellikleri, Post Graduate, S.BORA(Student), 2005

KASAP M., LEC tekniği ile büyütülen Te katkılı n-Tipi InSb yarıiletkeninde sıcaklık bağımlı manyetik ve elektron iletim özellikleri, Post Graduate, Ü.YURDUGÜL(Student), 2005

KASAP M., LEC tekniği ile büyütülen Te katkılı n-tipi GaSb yarı iletkeninde sıcaklık bağımlı manyetik ve elektron iletim özellikleri, Post Graduate, B.YASEMİN(Student), 2004

KASAP M., LEC tekniği ile büyütülen bulk InAs yarıiletkenin magneto ve elektron iletim özellikleri, Post Graduate, N.KEREM(Student), 2004

KASAP M., InAs yarıiletken kristalinde elektron iletimi, Post Graduate, D.DEMİR(Student), 2004

KASAP M., GaN yarıiletken kristalinde elektron iletimi, Post Graduate, A.YILDIZ(Student), 2004

KASAP M., GaAs ve InP yarıiletkenlerde elektriksel karakterizasyon, Doctorate, S.ACAR(Student), 2003

KASAP M., In<sub>0.51</sub>Ga<sub>0.49</sub>As ve In<sub>0.60</sub>Ga<sub>0.40</sub>As yarıiletkenlerinde mobilite hesaplamaları, Post Graduate, S.DEMİREZEN(Student), 2001

## Articles Published in Journals That Entered SCI, SSCI and AHCI Indexes

- I. **Temperature dependent electron transport properties of degenerate SnO<sub>2</sub> thin films**  
Boyalı E., Baran V., ASAR T., Ozcelik S., Kasap M.  
JOURNAL OF ALLOYS AND COMPOUNDS, vol.692, pp.119-123, 2017 (Journal Indexed in SCI)
- II. **Evaluation of morphological and chemical differences of gunshot residues in different ammunitions using SEM/EDS technique**  
Kara I., Sarikavak Y., LİŞESİVDİN S. B. , KASAP M.  
ENVIRONMENTAL FORENSICS, vol.17, no.1, pp.68-79, 2016 (Journal Indexed in SCI)
- III. **The Relationship Between the Surface Morphology and Chemical Composition of Gunshot Residue Particles**  
Kara I., LİŞESİVDİN S. B. , Kasap M., Er E., Uzek U.  
JOURNAL OF FORENSIC SCIENCES, vol.60, no.4, pp.1030-1033, 2015 (Journal Indexed in SCI)
- IV. **Electron Transport Properties of Two-Dimensional Electron Gas in Be<sub>x</sub>Zn<sub>1-x</sub>O/ZnO Heterostructures**  
Atmaca G., Narin P., Lisesivdin S. B. , Kasap M., Sarikavak-Lisesivdin B.  
PHILOSOPHICAL MAGAZINE, vol.95, no.1, pp.79-89, 2015 (Journal Indexed in SCI)
- V. **Study on growth and characterizations of Ga<sub>x</sub>In<sub>1-x</sub>P/GaAs solar cell structure**  
Kınacı B., Özen Y., Asar T., Cetin S. Ş. , Memmedli T., Kasap M., Ozcelik S.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, vol.24, no.9, pp.3269-3274, 2013 (Journal Indexed in SCI)

- VI. **Investigation of AlInN HEMT structures with different AlGa<sub>N</sub> buffer layers grown on sapphire substrates by MOCVD**  
Kelekci O., Tasli P., Cetin S. Ş. , Kasap M., Ozcelik S., Ozbay E.  
CURRENT APPLIED PHYSICS, vol.12, no.6, pp.1600-1605, 2012 (Journal Indexed in SCI)
- VII. **Electron transport properties in Al<sub>0.25</sub>Ga<sub>0.75</sub>N/AlN/GaN heterostructures with different InGa<sub>N</sub> back barrier layers and GaN channel thicknesses grown by MOCVD**  
Kelekci O., Tasli P. T. , Yu H., KASAP M., ÖZÇELİK S., ÖZBAY E.  
PHYSICA STATUS SOLIDI A-APPLICATIONS AND MATERIALS SCIENCE, vol.209, no.3, pp.434-438, 2012 (Journal Indexed in SCI)
- VIII. **Epitaxial growth and electrical characterization of germanium**  
Bosi M., Attolini G., Ferrari C., Frigeri C., Calicchio M., Gombia E., Asar T., Boyali E., Aydemir U., Ozcelik S., et al.  
CRYSTAL RESEARCH AND TECHNOLOGY, vol.46, no.8, pp.813-817, 2011 (Journal Indexed in SCI)
- IX. **Grain Boundary Related Electrical Transport in Al-rich Al<sub>x</sub>Ga<sub>1-x</sub>N Layers Grown by Metal-Organic Chemical Vapor Deposition**  
Yildiz A., Tasli P., Sarikavak B., Lisesivdin S. B. , Ozturk M. K. , Kasap M., Ozcelik S., Ozbay E.  
SEMICONDUCTORS, vol.45, no.1, pp.33-36, 2011 (Journal Indexed in SCI)
- X. **Electron-Electron Interactions in Sb-Doped SnO<sub>2</sub> Thin Films**  
Serin T., Yildiz A., SERİN N., Yildirim N., Ozyurt F., KASAP M.  
JOURNAL OF ELECTRONIC MATERIALS, vol.39, no.8, pp.1152-1158, 2010 (Journal Indexed in SCI)
- XI. **Scattering analysis of two-dimensional electrons in AlGa<sub>N</sub>/Ga<sub>N</sub> with bulk related parameters extracted by simple parallel conduction extraction method**  
Lişesivdin S. B. , Yildiz A., Balkan N., Kasap M., Ozcelik S., Ozbay E.  
JOURNAL OF APPLIED PHYSICS, vol.108, no.1, 2010 (Journal Indexed in SCI)
- XII. **The substrate temperature dependent electrical properties of titanium dioxide thin films**  
Yildiz A., LİŞESİVDİN S. B. , Kasap M., Mardare D.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, vol.21, no.7, pp.692-697, 2010 (Journal Indexed in SCI)
- XIII. **Double subband occupation of the two-dimensional electron gas in In<sub>x</sub>Al<sub>1-x</sub>N/AlN/GaN/AlN heterostructures with a low indium content (0.064 ≤ x ≤ 0.140) barrier**  
LİŞESİVDİN S. B. , Tasli P., Kasap M., Ozturk M., Arslan E., Ozcelik S., Ozbay E.  
THIN SOLID FILMS, vol.518, no.19, pp.5572-5575, 2010 (Journal Indexed in SCI)
- XIV. **Determination of the critical indium composition corresponding to the metal-insulator transition in In<sub>x</sub>Ga<sub>1-x</sub>N (0.06 ≤ x ≤ 0.135) layers**  
Yildiz A., LİŞESİVDİN S. B. , Tasli P., Ozbay E., Kasap M.  
CURRENT APPLIED PHYSICS, vol.10, no.3, pp.838-841, 2010 (Journal Indexed in SCI)
- XV. **The temperature dependence of the inelastic scattering time in InGa<sub>N</sub> grown by MOVPE**  
Yildiz A., Kasap M.  
LOW TEMPERATURE PHYSICS, vol.36, no.4, pp.320-324, 2010 (Journal Indexed in SCI)
- XVI. **Analysis of defect related optical transitions in biased AlGa<sub>N</sub>/Ga<sub>N</sub> heterostructures**  
Bengi A., LİŞESİVDİN S. B. , Kasap M., Mammadov T., Ozcelik S., Ozbay E.  
MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, vol.13, no.2, pp.105-108, 2010 (Journal Indexed in SCI)
- XVII. **The thickness effect on the electrical conduction mechanism in titanium oxide thin films**  
Yildiz A., Serin N., Kasap M., Serin T., Mardare D.  
JOURNAL OF ALLOYS AND COMPOUNDS, vol.493, pp.227-232, 2010 (Journal Indexed in SCI)
- XVIII. **Investigation of low-temperature electrical conduction mechanisms in highly resistive Ga<sub>N</sub> bulk layers extracted with Simple Parallel Conduction Extraction Method**  
Yildiz A., LİŞESİVDİN S. B. , Kasap M., Ozcelik S., Ozbay E., Balkan N.  
APPLIED PHYSICS A-MATERIALS SCIENCE & PROCESSING, vol.98, no.3, pp.557-563, 2010 (Journal Indexed in SCI)
- XIX. **Well parameters of two-dimensional electron gas in Al<sub>0.88</sub>In<sub>0.12</sub>N/AlN/GaN/AlN heterostructures grown by MOCVD**  
Tasli P., LİŞESİVDİN S. B. , Yildiz A., Kasap M., Arslan E., Ozcelik S., Ozbay E.

CRYSTAL RESEARCH AND TECHNOLOGY, vol.45, no.2, pp.133-139, 2010 (Journal Indexed in SCI)

- XX. **Contributions of impurity band and electron-electron interactions to magnetoconductance in AlGaN**  
Tasli P., Yildiz A., Kasap M., Ozbay E., LİŞESİVDİN S. B. , Ozcelik S.  
PHILOSOPHICAL MAGAZINE, vol.90, no.26, pp.3591-3599, 2010 (Journal Indexed in SCI)
- XXI. **Crossover from Nearest-Neighbor Hopping Conduction to Efros-Shklovskii Variable-Range Hopping Conduction in Hydrogenated Amorphous Silicon Films**  
Yildiz A., SERİN N., Serin T., KASAP M.  
JAPANESE JOURNAL OF APPLIED PHYSICS, vol.48, no.11, 2009 (Journal Indexed in SCI)
- XXII. **Electrical conduction properties of Si delta-doped GaAs grown by MBE**  
Yildiz A., LİŞESİVDİN S. B. , Altuntas H., Kasap M., Ozcelik S.  
PHYSICA B-CONDENSED MATTER, vol.404, no.21, pp.4202-4206, 2009 (Journal Indexed in SCI)
- XXIII. **The effect of intrinsic defects on the hole transport in Cu<sub>2</sub>O**  
Yildiz A., Serin N., Serin T., Kasap M.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, vol.3, no.10, pp.1034-1037, 2009 (Journal Indexed in SCI)
- XXIV. **Structural, electrical and optical characterization of InGaN layers grown by MOVPE**  
Yildiz A., Kemal O. M. , Bosi M., Ozcelik S., Kasap M.  
CHINESE PHYSICS B, vol.18, no.9, pp.4007-4012, 2009 (Journal Indexed in SCI)
- XXV. **DX-center energy calculation with quantitative mobility spectrum analysis in n-AlGaAs/GaAs structures with low Al content**  
LİŞESİVDİN S. B. , Altuntas H., Yildiz A., Kasap M., Ozbay E., Ozcelik S.  
SUPERLATTICES AND MICROSTRUCTURES, vol.45, no.6, pp.604-611, 2009 (Journal Indexed in SCI)
- XXVI. **Numerical optimization of Al-mole fractions and layer thicknesses in normally-on AlGaIn-GaN double-channel high electron mobility transistors (DCHEMTs)**  
Atmaca G., Elibol K., LİŞESİVDİN S. B. , Kasap M., Ozbay E.  
JOURNAL OF OPTOELECTRONICS AND ADVANCED MATERIALS, vol.11, no.5, pp.578-582, 2009 (Journal Indexed in SCI)
- XXVII. **Non-adiabatic small polaron hopping conduction in Nb-doped TiO<sub>2</sub> thin film**  
Yildiz A., LİŞESİVDİN S. B. , Kasap M., Mardare D.  
PHYSICA B-CONDENSED MATTER, vol.404, pp.1423-1426, 2009 (Journal Indexed in SCI)
- XXVIII. **Large zero-field spin splitting in AlGaIn/AlN/GaN/AlN heterostructures**  
LİŞESİVDİN S. B. , Balkan N., Makarovskiy O., Patane A., Yildiz A., Caliskan M. D. , Kasap M., Ozcelik S., Ozbay E.  
JOURNAL OF APPLIED PHYSICS, vol.105, no.9, 2009 (Journal Indexed in SCI)
- XXIX. **Anomalous temperature dependence of the electrical resistivity in In<sub>0.17</sub>Ga<sub>0.83</sub>N**  
Yildiz A., LİŞESİVDİN S. B. , Kasap M., Bosi M.  
SOLID STATE COMMUNICATIONS, vol.149, pp.337-340, 2009 (Journal Indexed in SCI)
- XXX. **Comparison of the transport properties of high quality AlGaIn/AlN/GaN and AlInN/AlN/GaN two-dimensional electron gas heterostructures**  
TÜLEK R., ILGAZ A., GÖKDEN S., TEKE A., Ozturk M. K. , KASAP M., Ozcelik S., Arslan E., ÖZBAY E.  
JOURNAL OF APPLIED PHYSICS, vol.105, no.1, 2009 (Journal Indexed in SCI)
- XXXI. **Electrical properties of TiO<sub>2</sub> thin films**  
Yildiz A., LİŞESİVDİN S. B. , Kasap M., Mardare D.  
JOURNAL OF NON-CRYSTALLINE SOLIDS, vol.354, pp.4944-4947, 2008 (Journal Indexed in SCI)
- XXXII. **Growth parameter investigation of Al<sub>0.25</sub>Ga<sub>0.75</sub>N/GaN/AlN heterostructures with Hall effect measurements**  
LİŞESİVDİN S. B. , Demirezen S., Caliskan M. D. , Yildiz A., Kasap M., Ozcelik S., Ozbay E.  
SEMICONDUCTOR SCIENCE AND TECHNOLOGY, vol.23, no.9, 2008 (Journal Indexed in SCI)
- XXXIII. **The persistent photoconductivity effect in AlGaIn/GaN heterostructures grown on sapphire and SiC substrates**  
Arslan E., Butun S., LİŞESİVDİN S. B. , KASAP M., ÖZÇELİK S., ÖZBAY E.  
JOURNAL OF APPLIED PHYSICS, vol.103, no.10, 2008 (Journal Indexed in SCI)

- XXXIV. **Determination of two-dimensional electron and hole gas carriers in AlGa<sub>N</sub>/Ga<sub>N</sub>/AlN heterostructures grown by Metal Organic Chemical Vapor Deposition**  
ACAR S., LİŞESİVDİN S. B. , Kasap M., Oezcelik S., Oezbay E.  
THIN SOLID FILMS, vol.516, no.8, pp.2041-2044, 2008 (Journal Indexed in SCI)
- XXXV. **Stokes shift and band gap bowing in In<sub>x</sub>Ga<sub>1-x</sub>N (0.060 ≤ x ≤ 0.105) grown by metalorganic vapour phase epitaxy**  
Yildiz A., Dagdelen F., ACAR S., LİŞESİVDİN S. B. , Kasap M., AYDOĞDU Y., Bosi M.  
ACTA PHYSICA POLONICA A, vol.113, no.2, pp.731-739, 2008 (Journal Indexed in SCI)
- XXXVI. **Self-consistent scattering analysis of Al<sub>0.2</sub>Ga<sub>0.8</sub>N/AlN/GaN/AlN heterostructures grown on 6H-SiC substrates using photo-Hall effect measurements**  
LİŞESİVDİN S. B. , Arslan E., Kasap M., Ozcelik S., Ozbay E.  
JOURNAL OF PHYSICS-CONDENSED MATTER, vol.20, no.4, 2008 (Journal Indexed in SCI)
- XXXVII. **The effect of strain relaxation on electron transport in undoped Al<sub>0.25</sub>Ga<sub>0.75</sub>N/GaN heterostructures**  
LİŞESİVDİN S. B. , Yildiz A., ACAR S., Kasap M., Oezcelik S., Oezbay E.  
PHYSICA B-CONDENSED MATTER, vol.399, no.2, pp.132-137, 2007 (Journal Indexed in SCI)
- XXXVIII. **Electron transport in Ga-rich In<sub>x</sub>Ga<sub>1-x</sub>N alloys**  
Yildiz A., LİŞESİVDİN S. B. , ACAR S., Kasap M., Bosi M.  
CHINESE PHYSICS LETTERS, vol.24, no.10, pp.2930-2933, 2007 (Journal Indexed in SCI)
- XXXIX. **Electronic transport characterization of AlGa<sub>N</sub>/Ga<sub>N</sub> heterostructures using quantitative mobility spectrum analysis**  
LİŞESİVDİN S. B. , Yildiz A., ACAR S., Kasap M., Ozcelik S., Ozbay E.  
APPLIED PHYSICS LETTERS, vol.91, no.10, 2007 (Journal Indexed in SCI)
- XL. **Temperature-dependent electron transport in In<sub>0.5</sub>Ga<sub>0.5</sub>P/GaAs grown by MOVPE**  
ACAR S., Yildiz A., Kasap M., Bosi M.  
CHINESE PHYSICS LETTERS, vol.24, no.8, pp.2373-2375, 2007 (Journal Indexed in SCI)
- XLI. **Scattering analysis of 2DEG carrier extracted by QMSA in undoped Al<sub>0.25</sub>Ga<sub>0.75</sub>N/GaN heterostructures**  
LİŞESİVDİN S. B. , ACAR S., Kasap M., Ozcelik S., Gokden S., Ozbay E.  
SEMICONDUCTOR SCIENCE AND TECHNOLOGY, vol.22, no.5, pp.543-548, 2007 (Journal Indexed in SCI)
- XLII. **High temperature variable-range hopping conductivity in undoped TiO<sub>2</sub> thin film**  
Yildiz A., LİŞESİVDİN S. B. , Kasap M., Mardare D.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, vol.1, no.10, pp.531-533, 2007 (Journal Indexed in SCI)
- XLIII. **Optimization of alloy composition, interlayer and barrier thicknesses in Al<sub>x</sub>Ga<sub>1-x</sub>N/(AlN)/Ga<sub>N</sub> high electron mobility transistors**  
LİŞESİVDİN S. B. , Yildiz A., Kasap M.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, vol.1, no.9, pp.467-470, 2007 (Journal Indexed in SCI)
- XLIV. **Quantitative mobility spectrum analysis for determination of electron and magneto transport properties of Te-doped GaSb**  
ACAR S., Kasap M., Isik B., Ozcelik S., Tugluoglu N., Karadeniz S.  
Chinese Physics Letters, vol.22, no.9, pp.2363-2366, 2005 (Journal Indexed in SCI Expanded)
- XLV. **Temperature-dependent galvanomagnetic measurements on doped InSb and InAs grown by liquid encapsulated czochralski**  
Kasap M., ACAR S., Ozcelik S., Karadeniz S., Tugluoglu N.  
Chinese Physics Letters, vol.22, no.5, pp.1218-1221, 2005 (Journal Indexed in SCI Expanded)
- XLVI. **The temperature dependence of electron and magneto transport properties in Te-doped InSb**  
Kasap M., ACAR S.  
PHYSICA STATUS SOLIDI A-APPLICATIONS AND MATERIALS SCIENCE, vol.201, no.14, pp.3113-3120, 2004 (Journal Indexed in SCI)

- XLVII. **Temperature-dependent barrier characteristics of inhomogeneous in/p-Si (100) Schottky barrier diodes**  
Tugluoglu N., Karadeniz S., ACAR S., Kasap M.  
CHINESE PHYSICS LETTERS, vol.21, no.9, pp.1795-1798, 2004 (Journal Indexed in SCI)
- XLVIII. **Gaussian distribution of inhomogeneous barrier height in Ag/p-Si (100) Schottky barrier diodes**  
ACAR S., Karadeniz S., Tugluoglu N., Selcuk A., Kasap M.  
APPLIED SURFACE SCIENCE, vol.233, pp.373-381, 2004 (Journal Indexed in SCI)
- XLIX. **Conductivity, Hall and magnetoresistance effect measurements on SiGaAs and InP**  
ACAR S., Kasap M.  
PHYSICA STATUS SOLIDI A-APPLIED RESEARCH, vol.201, no.7, pp.1551-1557, 2004 (Journal Indexed in SCI)
- L. **Prebreakdown current behaviour in the ionization cell with a semiconductor cathode**  
Salamov B., Kasap M., Lebedeva N.  
JOURNAL OF PHYSICS D-APPLIED PHYSICS, vol.33, no.17, pp.2192-2195, 2000 (Journal Indexed in SCI)
- LI. **The simulation of the two-dimensional Ising model in the presence of an external magnetic field on the Creutz cellular automaton**  
Kutlu B., Kasap M., Turan S.  
INTERNATIONAL JOURNAL OF MODERN PHYSICS C, vol.11, no.3, pp.561-572, 2000 (Journal Indexed in SCI)
- LII. **The concentration of currents on the artificial surface inhomogeneities of semiconducting cathodes in ionization cells**  
Salamov B., Ozer M., Kasap M., Altindal Ş.  
JOURNAL OF PHYSICS D-APPLIED PHYSICS, vol.32, no.6, pp.682-687, 1999 (Journal Indexed in SCI)
- LIII. **The temperature and pressure dependence of electron transport in plastically relaxed In<sub>x</sub>Ga<sub>1-x</sub>As**  
Kasap M., Lancefield D.  
PHYSICA STATUS SOLIDI B-BASIC RESEARCH, vol.199, no.2, pp.481-493, 1997 (Journal Indexed in SCI)
- LIV. **The rapid visualization of resistivity inhomogeneities in high-resistivity semiconductor films**  
Salamov B., Civi M., Altindal Ş., Kasap M., BULUR E.  
JOURNAL OF INFORMATION RECORDING, vol.23, no.5, pp.437-445, 1997 (Journal Indexed in SCI)
- LV. **Impurity conduction in In<sub>x</sub>Ga<sub>1-x</sub>As**  
KASAP M., ÖZER M., Çolakoğlu K.  
Turkish Journal of Physics, vol.20, no.7, pp.740-746, 1996 (Journal Indexed in SCI Expanded)

## Articles Published in Other Journals

- I. **Analysis Of The Number Of Shots Using Graphite Furnace Atomic Absorption Spectrometry On The Gunshot Residues Deposited in The Barrel**  
KARA İ., YALÇINKAYA Ö., LİSESİVDİN S. B. , KASAP M.  
SYLWAN, vol.159, no.1, pp.14-26, 2015 (Refereed Journals of Other Institutions)

## Refereed Congress / Symposium Publications in Proceedings

- I. **The Study on Antimony Diffusion in Gallium-Doped Germanium Grown by Chochralski Technique**  
Baran V., Çat Y., Akın Sönmez N., Özen Y., Kasap M., Özçelik S.  
Turkish Physical Society 33th International Physics Congress, Muğla, Turkey, 6 - 10 September 2017
- II. **The Study on Antimony Diffusion in Gallium-doped Germanium Grown by Czochralski Technique**  
Baran V., Çat Y., Akın Sönmez N., Özen Y., Kasap M., Özçelik S.  
Turkish Physical Society 33th International Physics Congress (TFD33), Muğla, Turkey, 6 - 10 September 2017
- III. **Germanyum Kızıl Ötesi Optik Pencereleer ve Elektromanyetik Girişim**  
Çat Y., Baran V., Kasap M., Özçelik S.  
22. Yoğun Madde Fiziği Ankara Toplantısı, Ankara, Turkey, 16 December 2016

- IV. **Pt Metal Kümelerin Katkısız SnO<sub>2</sub> Sensör Yapılarının Algılama Özelliklerine Etkisi**  
Boyalı E., Korkmaz B., Sertel T., Efkere H. İ., Özen Y., Çetin S. Ş., Özçelik S., Kasap M.  
22. Yoğun Madde Fiziği Ankara Toplantısı, Ankara, Turkey, 16 December 2016
- V. **Sb Doping Effect on the Electrical Properties of Germanium Single Crystals**  
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## **Supported Projects**

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